2:1 Mux/Demux Analog Switches

The NLAS1053 is an advanced CMOS analog switch fabricated with silicon gate CMOS technology. It achieves very high speed propagation delays and low ON resistances while maintaining CMOS low power dissipation. The device consists of a single 2:1 Mux/Demux (SPDT), similar to ON Semiconductor's NLAS4053 analog and digital voltages that may vary across the full power supply range (from $V_{\rm CC}$ to GND).

The inhibit and select input pins have over voltage protection that allows voltages above V_{CC} up to 7.0 V to be present without damage or disruption of operation of the part, regardless of the operating voltage.

Features

- High Speed: $t_{PD} = 1$ ns (Typ) at $V_{CC} = 5.0$ V
- Low Power Dissipation: $I_{CC} = 2 \mu A$ (Max) at $T_A = 25^{\circ}C$
- High Bandwidth, Improved Linearity, and Low RDS_{ON}
- INH Pin Allows a Both Channels 'OFF' Condition (With a High)
- RDS_{ON} \cong 25 Ω , Performance Very Similar to the NLAS4053
- Break Before Make Circuitry, Prevents Inadvertent Shorts
- Useful For Switching Video Frequencies Beyond 50 MHz
- Latchup Performance Exceeds 300 mA
- ESD Performance: HBM > 2000 V; MM > 200 V, CDM > 1500 V
- Tiny US8 Package, Only 2.1 X 3.0 mm
- Pb-Free Package is Available

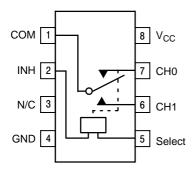


Figure 1. Pin Assignment



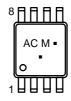
ON Semiconductor®

http://onsemi.com



US8 US SUFFIX CASE 493-01

MARKING DIAGRAMS



AC = Specific Device Code

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
NLAS1053US	US8	3000 / Tape & Reel
NLAS1053USG	US8 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

FUNCTION TABLE

INH	Select	Ch 0	Ch 1
Н	Х	OFF	OFF
L	L	ON	OFF
L	Н	OFF	ON

MAXIMUM RATINGS

	Parameter	Symbol	Value	Unit
Positive DC Supply Voltage		V _{CC}	-0.5 to +7.0	V
Digital Input Voltage (Select a	nd Inhibit)	V_{IN}	$-0.5 \le V \text{ is } \le +7.0$	V
Analog Output Voltage (V _{CH}	or V _{COM})	V _{IS}	$-0.5 \le V \text{ is } \le V_{CC} + 0.5$	V
DC Current, Into or Out of An	y Pin	I _{IK}	50	mA
Storage Temperature Range		T _{STG}	-65 to +150	°C
Lead Temperature, 1 mm from	n Case for 10 Seconds	TL	260	°C
Junction Temperature under E	Bias	TJ	+150	°C
Thermal Resistance		θ_{JA}	250	°C/W
Power Dissipation in Still Air a	at 85°C	P_{D}	250	mW
Moisture Sensitivity		MSL	Level 1	
Flammability Rating	Oxygen Index: 30% – 35%	F _R	UL 94 V-0 @ 0.125 in	
ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	V _{ESD}	> 2000 200 N/A	V
Latchup Performance	Above V _{CC} and Below GND at 85°C (Note 5)	I _{Latchup}	±300	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.
- 2. Tested to EIA/JESD22-A114-A.
- 3. Tested to EIA/JESD22-A115-A.
- 4. Tested to JESD22-C101-A.
- 5. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Characteristics	Symbol	Min	Max	Unit	
Positive DC Supply Voltage		V _{CC}	2.0	5.5	V
Digital Input Voltage (Select and Inhibit)		V _{IN}	GND	5.5	V
Static or Dynamic Voltage Across an Off Switch		V _{IO}	GND	V _{CC}	V
Analog Input Voltage (CH, COM)		V _{IS}	GND	V _{CC}	V
Operating Temperature Range, All Package Types		T _A	-55	+125	°C
Input Rise or Fall Time (Enable Input)	$V_{cc} = 3.3 \text{ V} \pm 0.3 \text{ V}$ $V_{cc} = 5.0 \text{ V} \pm 0.5 \text{ V}$	t _r , t _f	0 0	100 20	ns/V

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

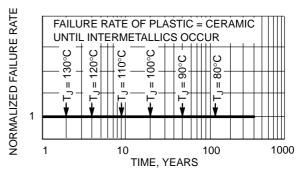


Figure 2. Failure Rate versus Time Junction Temperature

DC CHARACTERISTICS – Digital Section (Voltages Referenced to GND)

				Guaranteed Limit			
Parameter	Condition	Symbol	V _{CC}	-55°C to 25°C	<85°C	<125°C	Unit
Minimum High-Level Input Voltage, Select and Inhibit Inputs		V _{IH}	2.0 2.5 3.0 4.5 5.5	1.5 1.9 2.1 3.15 3.85	1.5 1.9 2.1 3.15 3.85	1.5 1.9 2.1 3.15 3.85	V
Maximum Low–Level Input Voltage, Select and Inhibit Inputs		V _{IL}	2.0 2.5 3.0 4.5 5.5	0.5 0.6 0.9 1.35 1.65	0.5 0.6 0.9 1.35 1.65	0.5 0.6 0.9 1.35 1.65	V
Maximum Input Leakage Current, Select and Inhibit Inputs	V _{IN} = 5.5 V or GND	I _{IN}	0 V to 5.5 V	±0.1	±1.0	±1.0	μΑ
Maximum Quiescent Supply Current	Select and Inhibit = V _{CC} or GND	Icc	5.5	1.0	1.0	2.0	μΑ

DC ELECTRICAL CHARACTERISTICS - Analog Section

				Guara	nteed Limit	t	
Parameter	Condition	Symbol	V _{CC}	−55 to 25°C	< 85°C	< 125°C	Unit
Maximum "ON" Resistance (Figures 17 – 23)	$ \begin{aligned} &V_{IN} = V_{IL} \text{ or } V_{IH} \\ &V_{IS} = GND \text{ to } V_{CC} \\ &I_{IN}I \leq 10.0 \text{ mA} \end{aligned} $	R _{ON}	2.5 3.0 4.5 5.5	70 40 20 16	85 46 28 22	105 52 34 28	Ω
ON Resistance Flatness (Figures 17 – 23)	$\begin{aligned} &V_{IN} = V_{IL} \text{ or } V_{IH} \\ &I_{IN}I \leq 10.0 \text{ mA} \\ &V_{IS} = 1V, 2V, 3.5V \end{aligned}$	R _{FLAT} (ON)	4.5	4	4	5	Ω
ON Resistance Match Between Channels	$\begin{aligned} &V_{IN} = V_{IL} \text{ or } V_{IH} \\ &I_{IN}I \leq 10.0 \text{ mA} \\ &V_{CH1} \text{ or } V_{CH0} = 3.5 \text{ V} \end{aligned}$	ΔR _{ON} (ON)	4.5	2	2	3	Ω
CH1 or CH0 Off Leakage Current (Figure 9)	$V_{IN} = V_{IL} \text{ or } V_{IH}$ $V_{CH1} \text{ or } V_{CH0} = 1.0 V_{COM} \text{ 4.5 V}$	I _{CH0} I _{CH1}	5.5	1	10	100	nA
COM ON Leakage Current (Figure 9)	$\begin{aligned} &V_{IN} = V_{IL} \text{ or } V_{IH} \\ &V_{CH1} \text{ 1.0 V or 4.5 V with } V_{CH0} \\ &\text{floating or} \\ &V_{CH1} \text{ 1.0 V or 4.5 V with } V_{CH1} \\ &\text{floating} \\ &V_{COM} = 1.0 \text{ V or 4.5 V} \end{aligned}$	I _{COM(ON)}	5.5	1	10	100	nA

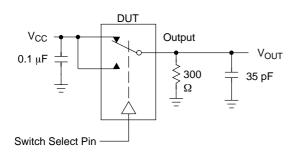
AC ELECTRICAL CHARACTERISTICS (Input $t_{\text{f}} = t_{\text{f}} = 3.0 \text{ ns}$)

				Guaranteed Max Limit							
			V _{CC}	-5	5 to 25	°C	< 8	5°C	< 12	5°C	
Parameter	Test Conditions	Symbol	(V)	Min	Тур*	Max	Min	Max	Min	Max	Unit
Turn-On Time (Figures 12 and 13) INH to Output	$R_L = 300 \Omega$, $C_L = 35 pF$ (Figures 4 and 5)	t _{ON}	2.5 3.0 4.5 5.5	2 2 1 1	7 5 4 3	12 10 9 8	2 2 1 1	15 15 12 12	2 2 1 1	15 15 12 12	ns
Turn-Off Time (Figures 12 and 13) INH to Output	$R_L = 300 \Omega$, $C_L = 35 pF$ (Figures 4 and 5)	tOFF	2.5 3.0 4.5 5.5	2 2 1 1	7 5 4 3	12 10 9 8	2 2 1 1	15 15 12 12	2 2 1 1	15 15 12 12	ns
Transition Time (Channel Selection Time) (Figure) Select to Output	$R_L = 300 \Omega$, $C_L = 35 pF$ (Figures and)	t _{trans}	2.5 3.0 4.5 5.5	5 5 2 2	18 13 12 9	28 21 16 14	5 5 2 2	30 25 20 20	5 5 2 2	30 25 20 20	ns
Minimum Break-Before-Make Time	V_{IS} = 3.0 V (Figure 3) R_L = 300 Ω , C_L = 35 pF	t _{BBM}	2.5 3.0 4.5 5.5	1 1 1	12 11 6 5		1 1 1		1 1 1		ns
			Typical @ 25, VCC = 5.0 V								
Maximum Input Capacitance, Select/INH Input Analog I/O (switch off) Common I/O (switch off) Feedthrough (switch on)		C _{IN} C _{NO} or C _{NC} C _{COM} C _(ON)	8 10 10 20					pF			

^{*}Typical Characteristics are at 25°C.

ADDITIONAL APPLICATION CHARACTERISTICS (Voltages Referenced to GND Unless Noted)

			V _{CC}	Typical	
Parameter	Condition	Symbol	V	25°C	Unit
Maximum On–Channel –3dB Bandwidth or Minimum Frequency Response (Figure 10)	V_{IN} = 0 dBm V_{IN} centered between V_{CC} and GND (Figure 7)	BW	3.0 4.5 5.5	170 200 200	MHz
Maximum Feedthrough On Loss	V_{IN} = 0 dBm @ 100 kHz to 50 MHz V_{IN} centered between V_{CC} and GND (Figure 7)	V _{ONL}	3.0 4.5 5.5	-3 -3 -3	dB
Off-Channel Isolation (Figure 10)		V _{ISO}	3.0 4.5 5.5	-93 -93 -93	dB
Charge Injection Select Input to Common I/O (Figure 15)	$\begin{aligned} &V_{IN} = V_{CC\ to}\ \text{GND},\ F_{IS} = 20\ \text{kHz} \\ &t_r = t_f = 3\ \text{ns} \\ &R_{IS} = 0\ \Omega,\ C_L = 1000\ \text{pF} \\ &Q = C_L * \Delta V_{OUT} \\ &(\text{Figure 8}) \end{aligned}$	Q	3.0 5.5	1.5 3.0	рС
Total Harmonic Distortion THD + Noise (Figure 14)	F_{IS} = 20 Hz to 100 kHz, RL = Rgen = 600 Ω C_L = 50 pF V_{IS} = 5.0 V_{PP} sine wave	THD	5.5	0.1	%



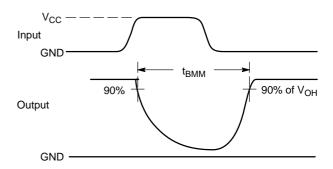
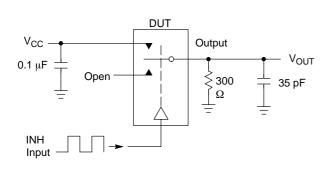


Figure 3. t_{BBM} (Time Break-Before-Make)



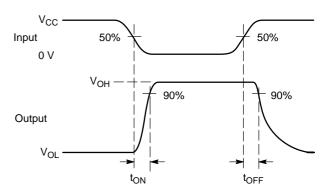
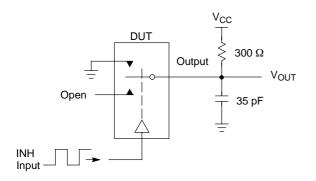


Figure 4. t_{ON}/t_{OFF}



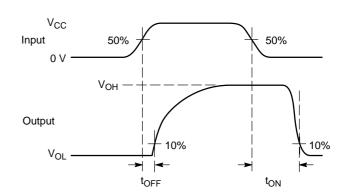


Figure 5. t_{ON}/t_{OFF}

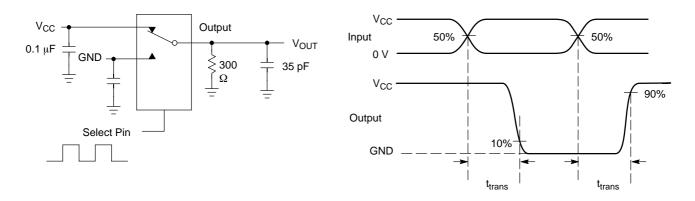
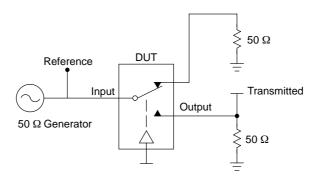


Figure 6. t_{trans} (Channel Selection Time)



Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch. $V_{\rm ISO}$, Bandwidth and $V_{\rm ONL}$ are independent of the input signal direction.

$$\begin{split} &V_{ISO} = \text{Off Channel Isolation} = 20 \text{ Log } \left(\frac{\text{VOUT}}{\text{V}_{IN}} \right) \text{ for V}_{IN} \text{ at 100 kHz} \\ &V_{ONL} = \text{On Channel Loss} = 20 \text{ Log } \left(\frac{\text{VOUT}}{\text{V}_{IN}} \right) \text{ for V}_{IN} \text{ at 100 kHz to 50 MHz} \end{split}$$

Bandwidth (BW) = the frequency 3 dB below V_{ONL}

Figure 7. Off Channel Isolation/On Channel Loss (BW)/Crosstalk (On Channel to Off Channel)/V_{ONL}

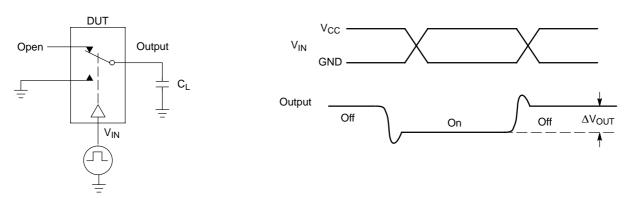
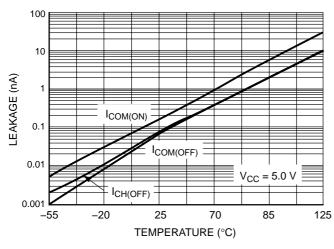


Figure 8. Charge Injection: (Q)

-20

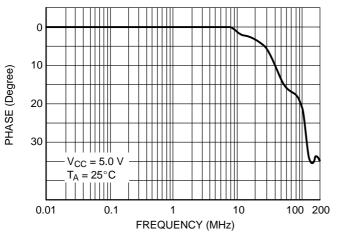


-40 Off Isolation
-60 V_{CC} = 5.0 V
T_A = 25°C
-100 0.01 0.1 1 10 100 200
FREQUENCY (MHz)

Bandwidth (ON-RESPONSE)

Figure 9. Switch Leakage versus Temperature

Figure 10. Bandwidth and Off-Channel Isolation



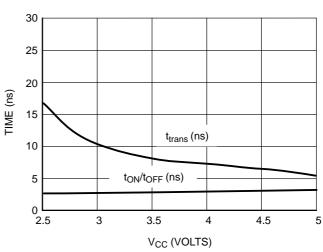
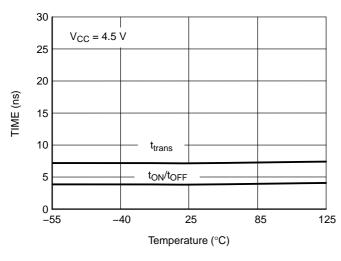


Figure 11. Phase versus Frequency

Figure 12. t_{ON} and t_{OFF} versus V_{CC} at 25°C



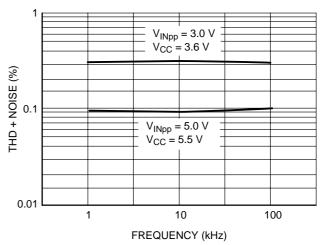


Figure 13. t_{ON} and t_{OFF} versus Temp

Figure 14. Total Harmonic Distortion Plus Noise versus Frequency

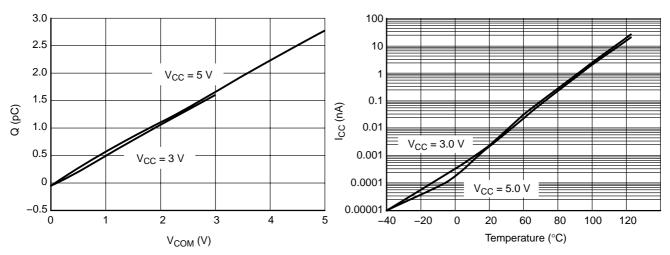


Figure 15. Charge Injection versus COM Voltage

Figure 16. I_{CC} versus Temp, V_{CC} = 3 V & 5 V

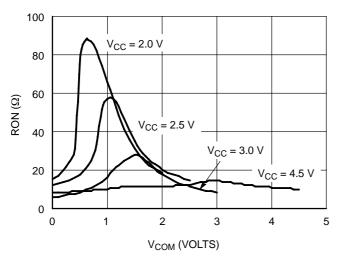


Figure 17. R_{ON} versus V_{COM} and $V_{CC\,(@}\,25^{\circ}C$

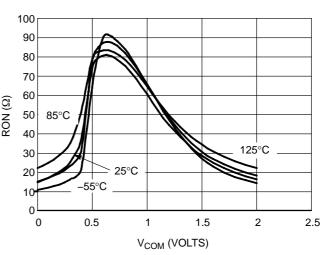


Figure 18. R_{ON} versus V_{COM} and Temperature, $V_{CC}\,2.0\;V$

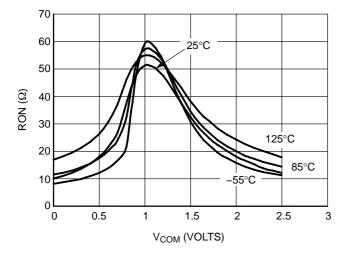


Figure 19. R_{ON} versus V_{COM} and Temperature, V_{CC} = 2.5 V

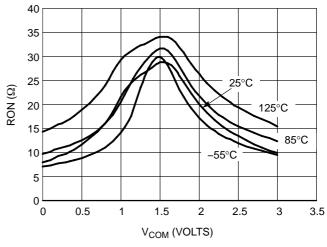
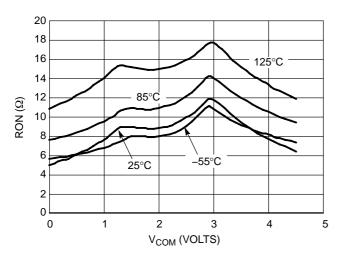


Figure 20. $R_{\mbox{\scriptsize ON}}$ versus $V_{\mbox{\scriptsize COM}}$ and Temperature, $V_{\mbox{\scriptsize CC}} = 3.0~\mbox{\scriptsize V}$



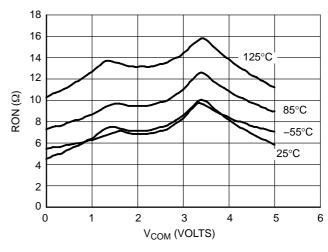


Figure 21. R_{ON} versus V_{COM} and Temperature, V_{CC} = 4.5 V

Figure 22. R_{ON} versus V_{COM} and Temperature, V_{CC} = 5.0 V

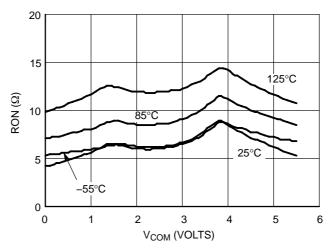
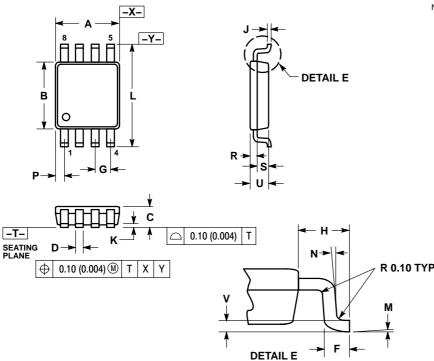


Figure 23. R_{ON} versus V_{COM} and Temperature, V_{CC} = 5.5 V

PACKAGE DIMENSIONS

US8 CASE 493-02 **ISSUE B**



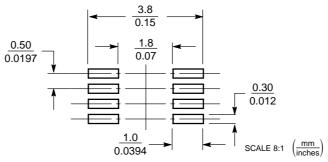
NOTES

- DIMENSIONING AND TOLERANCING PER
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETERS. DIMENSION "A" DOES NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURR.
 MOLD FLASH, PROTRUSION AND GATE BURR SHALL NOT EXCEED 0.140 MM (0.0055") PER SIDE.
- DIMENSION "B" DOES NOT INCLUDE INTER-LEAD FLASH OR PROTRUSION. INTER-LEAD FLASH AND PROTRUSION. SHALL NOT E3XCEED 0.140 (0.0055") PER
- SIDE.

 LEAD FINISH IS SOLDER PLATING WITH THICKNESS OF 0.0076–0.0203 MM.
- (300–800 "). ALL TOLERANCE UNLESS OTHERWISE SPECIFIED ±0.0508 (0.0002 ").

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	1.90	2.10	0.075	0.083	
В	2.20	2.40	0.087	0.094	
С	0.60	0.90	0.024	0.035	
D	0.17	0.25	0.007	0.010	
F	0.20	0.35	0.008	0.014	
G	0.50	BSC	0.020	BSC	
Н	0.40	REF	0.016	REF	
J	0.10	0.18	0.004	0.007	
K	0.00	0.10	0.000	0.004	
L	3.00	3.20	0.118	0.126	
M	0 °	6 °	0 °	6°	
N	5°	10 °	5°	10 °	
P	0.23	0.34	0.010	0.013	
R	0.23	0.33	0.009	0.013	
S	0.37	0.47	0.015	0.019	
U	0.60	0.80	0.024	0.031	
V	0.12	BSC	0.005 BSC		

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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